



DUAL SURFACE MOUNT NPN/PNP TRANSISTORS (COMPLEMENTARY)

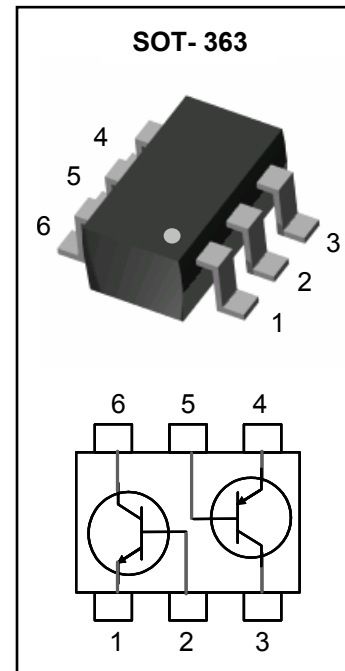
This device contains two electrically-isolated complimentary pair (NPN and PNP) general-purpose transistors. This device is ideal for portable applications where board space is at a premium.

FEATURES

- Electrically-Isolated Complimentary Transistor Pairs
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard
- AEC-Q101 qualified

APPLICATIONS

- General Purpose Amplifier Applications
- Hand-Held Computers, PDAs



MAXIMUM RATINGS - NPN

$T_J = 25^{\circ}\text{C}$ Unless otherwise noted

Rating	Symbol	Value	Units
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage Voltage	V_{EBO}	6.0	V
Collector Current	I_C	100	mA

MAXIMUM RATINGS - PNP

$T_J = 25^{\circ}\text{C}$ Unless otherwise noted

Rating	Symbol	Value	Units
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-100	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P_D	200	mW
Operating Junction Temperature Range	T_J	-55 to +150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}\text{C}$
Thermal Resistance, Junction to Ambient (Note 1)	R_{thja}	556	$^{\circ}\text{C}/\text{W}$

Note 1. FR-4 board 70 x 60 x 1mm with minimum recommended pad layout



NPN ELECTRICAL CHARACTERISTICS (Note 2)

T_J = 25°C Unless otherwise noted

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10mA$	45	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C = 10\mu A, V_{EB} = 0$	50	-	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu A$	50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 1.0\mu A$	6.0	-	-	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 30V, I_E = 0$ $T_J = 150^\circ C$	-	-	15	nA
			-	-	5	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	-	-	100	nA
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 2.0mA$	200	-	450	-
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = 10mA, I_B = 0.5mA$ $I_C = 100mA, I_B = 5mA$	-	-	0.1	V
			-	-	0.4	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = 10mA, I_B = 0.5mA$	-	0.75	-	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 5V, I_C = 2.0mA$	0.58	-	0.7	V
Gain-Bandwidth Product	f_T	$V_{CE} = 5V, I_C = 10mA$ $f = 100MHz$	100	-	-	MHz
Collector-Base Capacitance	C_{CBO}	$V_{CB} = 10V, f = 1.0MHz$	-	-	1.5	pF
Emitter-Base Capacitance	C_{EBO}	$V_{EB} = 0.5V, f = 1.0MHz$	-	7	-	pF

PNP ELECTRICAL CHARACTERISTICS (Note 2)

T = 25°C Unless otherwise noted

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA$	-45	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C = -10\mu A, V_{EB} = 0$	-50	-	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu A$	-50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1.0\mu A$	-5.0	-	-	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = -30V, I_E = 0$ $T_J = 150^\circ C$	-	-	-15	nA
			-	-	-4.0	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	-	-	-100	nA
DC Current Gain	h_{FE}	$V_{CE} = -5V, I_C = -2.0mA$	200	-	475	-
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -10mA, I_B = -0.5mA$ $I_C = -100mA, I_B = -5mA$	-	-	-0.3	V
			-	-	-0.65	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = -10mA, I_B = -0.5mA$	-	-0.7	-	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -5V, I_C = -2.0mA$	-0.6	-	-0.75	V
Gain-Bandwidth Product	f_T	$V_{CE} = -5V, I_C = -10mA$ $f = 100MHz$	100	-	-	MHz
Collector-Base Capacitance	C_{CBO}	$V_{CB} = -10V, f = 1.0MHz$	-	-	4.5	pF
Emitter-Base Capacitance	C_{EBO}	$V_{EB} = -0.5V, f = 1.0MHz$	-	11	-	pF

Note 2. Short duration test pulse used to minimize self-heating



ELECTRICAL CHARACTERISTICS CURVE

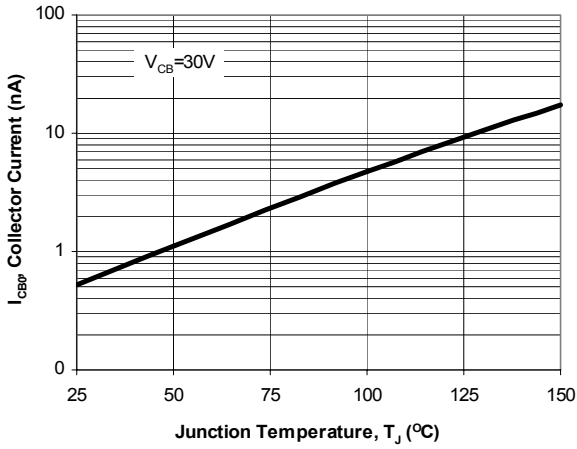


Fig. 1. Typical I_{CB0} vs. Junction Temperature

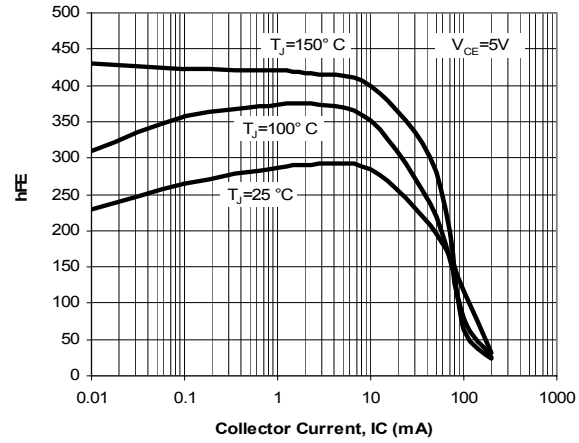


Fig. 2. Typical h_{FE} vs. Collector Current

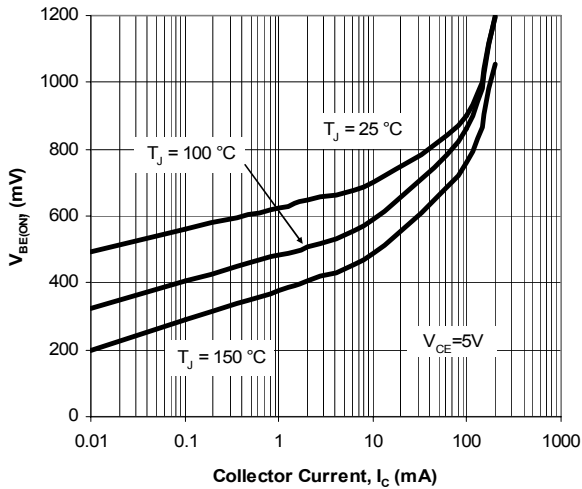


Fig. 3. Typical $V_{BE(ON)}$ vs. Collector Current

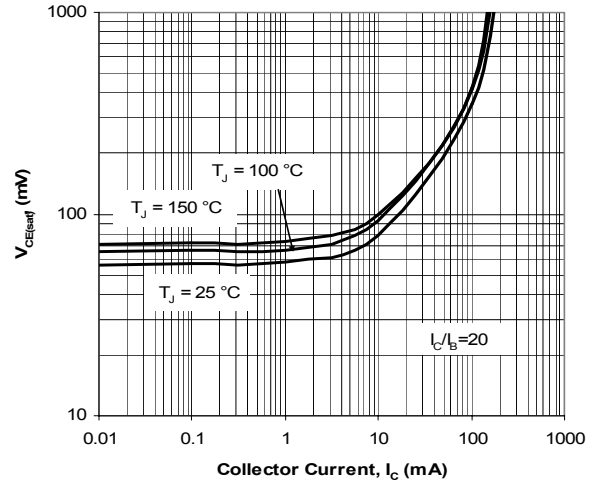


Fig. 4. Typical $V_{CE(SAT)}$ vs. Collector Current

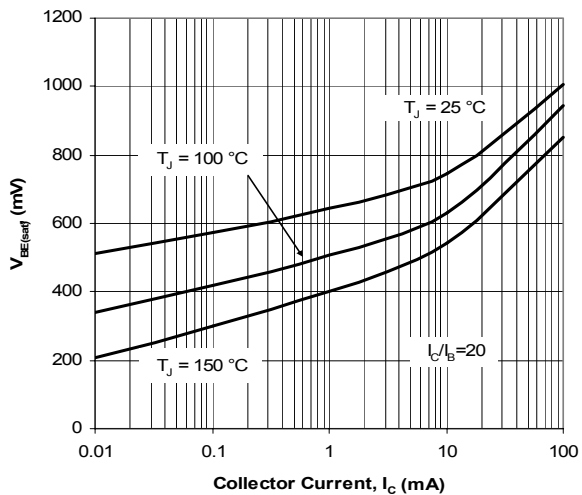


Fig. 5. Typical $V_{BE(SAT)}$ vs. Collector Current

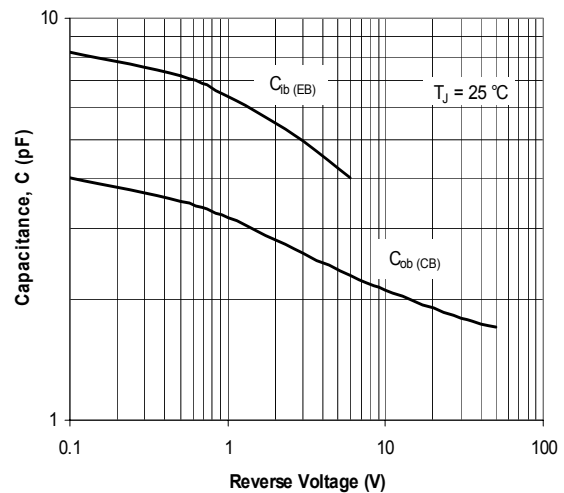


Fig. 6. Typical Capacitances vs. Reverse Voltage

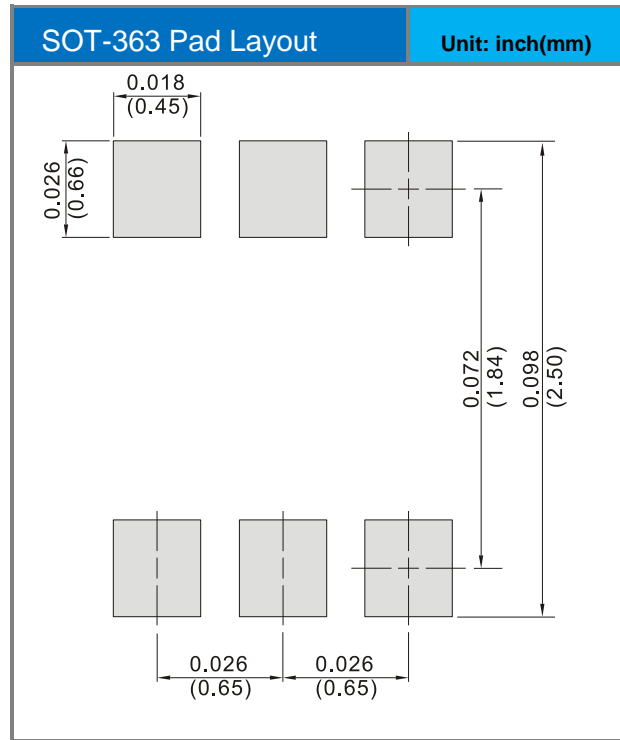
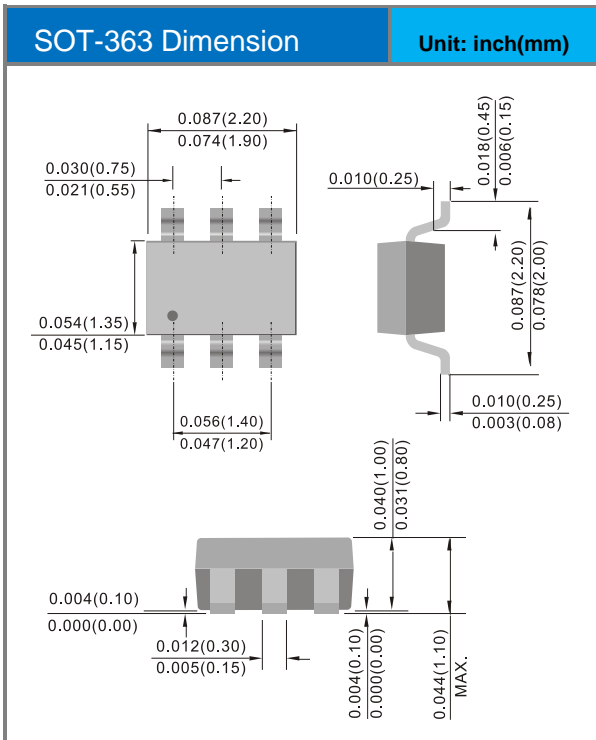


BC847BPN-AU

Product and Packing Information

Part No.	Package Type	Packing Type	Marking
BC847BPN-AU	SOT-363	3K pcs / 7" reel	47P
BC847BPN-AU	SOT-363	10K pcs / 13" reel	47P

Packaging Information & Mounting Pad Layout





BC847BPN-AU

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